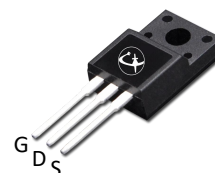
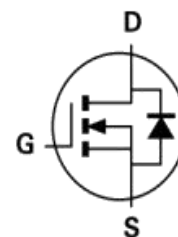


MAIN CHARACTERISTICS

I_D	5A
V_{DSS}	650V
$R_{DS(on)}$ -typ (@VGS=10V Tc=25°C)	900mΩ



TO-220F

FEATURES

- Ultra low RDS(on)
- Ultra low gate charge (typ. Qg=10nC)
- 100% UIS tested

APPLICATIONS

- Power factor correction (PFC)
- Switched mode power supplies (SMPS)
- Uninterruptible power supply (UPS)

MECHANICAL DATA

- Case: Molded plastic
- Mounting Position: Any
- Molded Plastic: UL Flammability Classification Rating 94V-0
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Solder bath temperature 275°C maximum, 10s per JESD 22-B106

Product specification classification

Part Number	Package	Mode Name	Pack
LC65R950F	TO-220F	LC65R950F	Tube

Maximum Ratings at Tc=25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	±30	V
Continue Drain Current	I_D	5	A
Pulsed Drain Current (Note1)	I_{DM}	15	A
Power Dissipation	P_D	60	W
Single Pulse Avalanche Energy (Note1)	E_{AS}	120	mJ
Operating Temperature Range	T_J	-55 to +150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Thermal Resistance, Junction to Case	$R_{\theta JC}$	5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62	°C/W

Note1:Pulse test: 300 μ s pulse width, 2 % duty cycle

Electrical Characteristics at Tc=25°C unless otherwise specified

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV_{DSS}	650	-	-	V
Drain-Source Leakage Current	$V_{DS} = 650V, V_{GS} = 0V$	I_{DSS}	-	-	1	μA
Gate Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$	I_{GSS}	-	-	±100	nA
Gate-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	$V_{GS(th)}$	2.5	3.67	4.5	V
Drain-Source On-State Resistance	$V_{GS}=10V, I_D=2A$	$R_{DS(on)}$	-	900	950	m Ω
Input Capacitance	$V_{DS}=100V, V_{GS}=0V, f=250KHz$	C_{iss}	-	357	-	pF
Output Capacitance		C_{oss}	-	16	-	pF
Reverse Transfer Capacitance		C_{rss}	-	0.42	-	pF
Turn-on Delay Time(Note2)	$V_{DD} = 400V, I_D = 2A, V_{GS} = 10V, R_G = 10\Omega$	$t_{d(ON)}$	-	26	-	ns
Rise Time(Note2)		t_r	-	11	-	ns
Turn-Off Delay Time(Note2)		$t_{d(OFF)}$	-	25	-	ns
Fall Time(Note2)		t_f	-	35	-	ns
Total Gate Charge(Note2)	$V_{DS} = 520V, V_{GS} = 10V, I_D = 2A$	Q_G	-	10	-	nC
Gate to Source Charge(Note2)		Q_{GS}	-	1.9	-	nC
Gate to Drain Charge(Note2)		Q_{GD}	-	5	-	nC

Source-Drain Diode Characteristics at Ta=25°C unless otherwise specified

Parameter	Test Condition	Symbol	Min.	Typ.	Max.	Unit
Maximun Body-Diode Continuous Current		I_S	-	-	5	A
Maximun Body-Diode Pulsed Current(Note2)		I_{SM}	-	-	15	A
Drain-Source Diode Forward Voltage	$V_{GS}=0V, I_S=2A, T_J=25^\circ C$	V_{SD}	-	-	1.1	V
Body Diode Reverse Recovery Time	$V_R=400V, I_F=2A, di/dt=100A/\mu s$	T_{rr}	-	191	-	ns
Body Diode Reverse Recovery Charge		Q_{rr}	-	858	-	μC
Peak reverse recovery current		I_{rrm}	-	10.5	-	A

Note2:Pulse test: 300 μ s pulse width, 2 % duty cycle

Fig 1: Output Characteristics

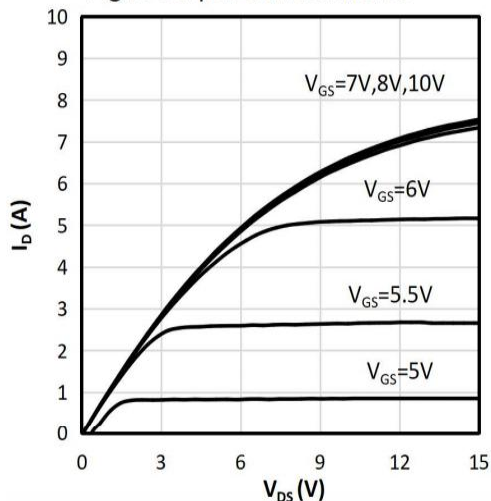


Fig 2: Transfer Characteristics

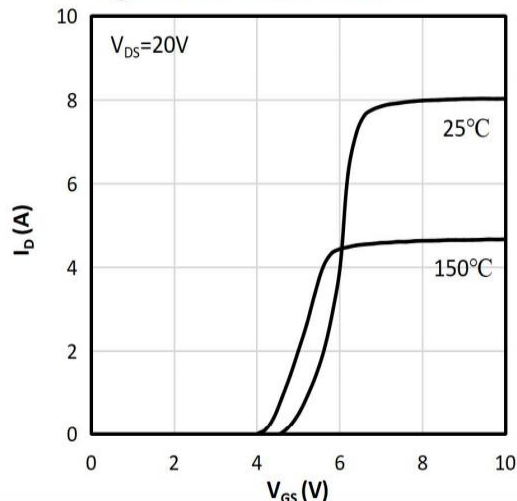


Fig 3: $R_{DS(on)}$ vs Drain Current

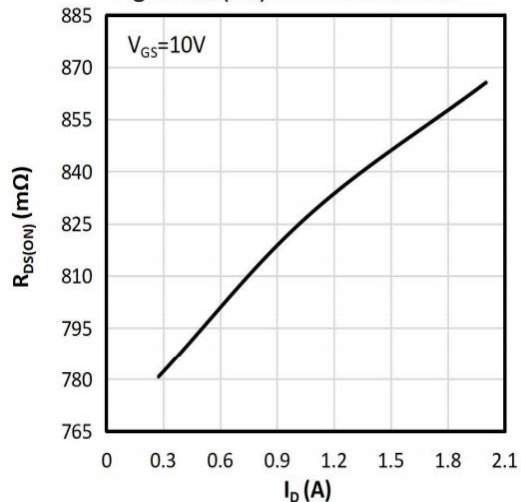


Fig 4: $R_{DS(on)}$ vs. Temperature

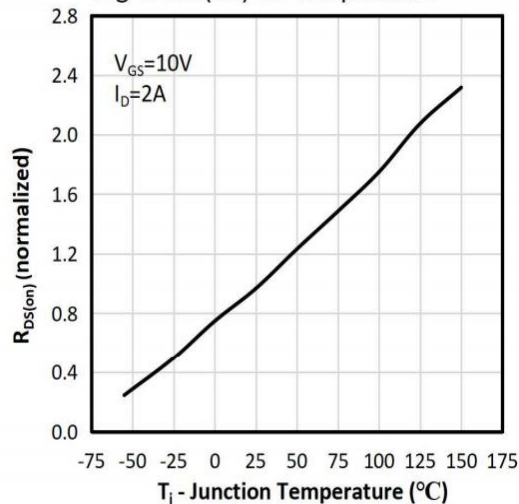


Fig 5: Breakdown Voltage vs. Temperature

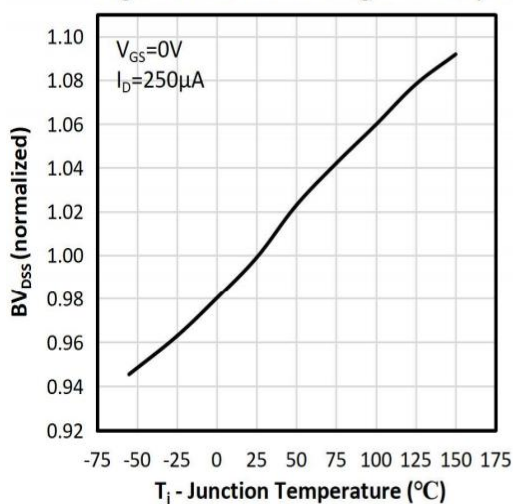
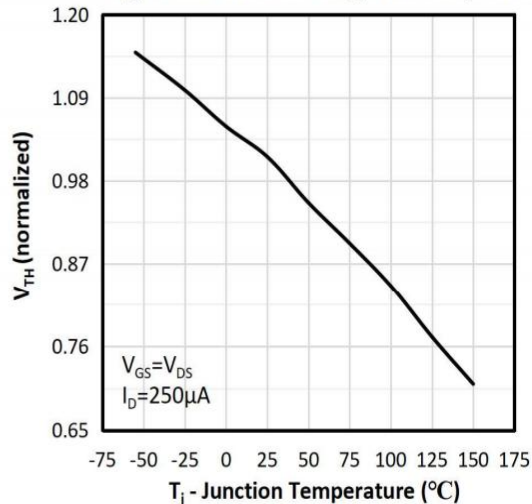


Fig 6: Threshold voltage vs. Temperature



RATINGS AND CHARACTERISTIC CURVES

Fig 7: Body-Diode Characteristics

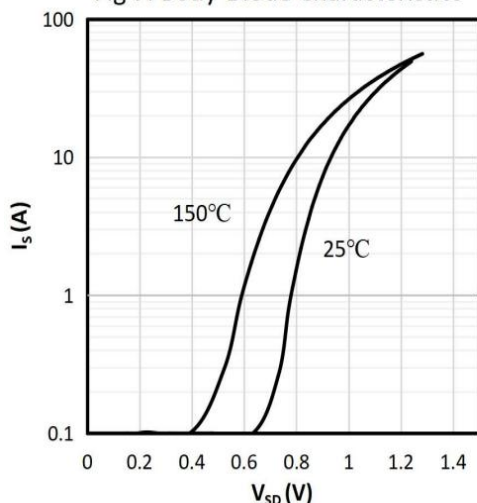


Fig 8: Capacitance Characteristics

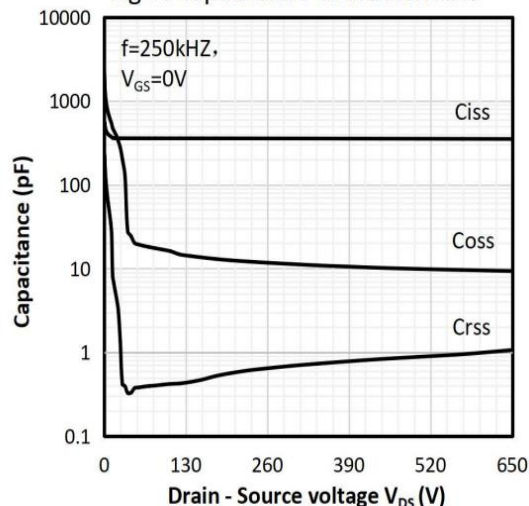


Fig 9: Gate charger Characteristics

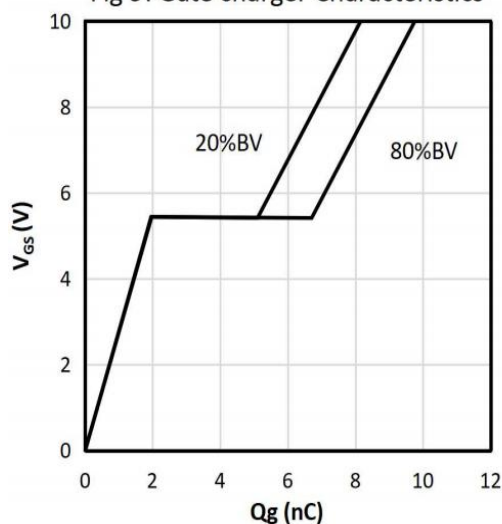


Fig 10: Drain Current Derating

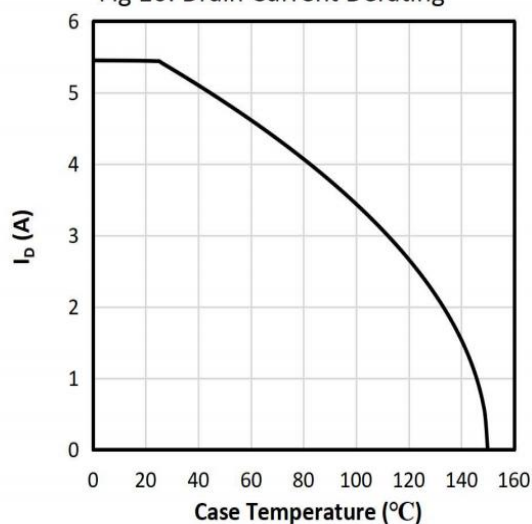


Fig 11: Power Dissipation vs. Temperature

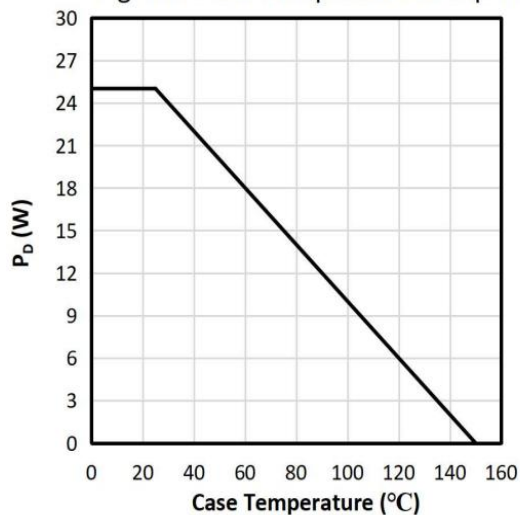


Fig 12: Safe Operating Area

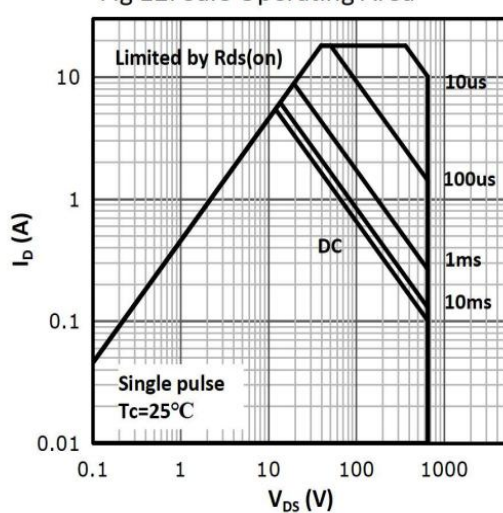
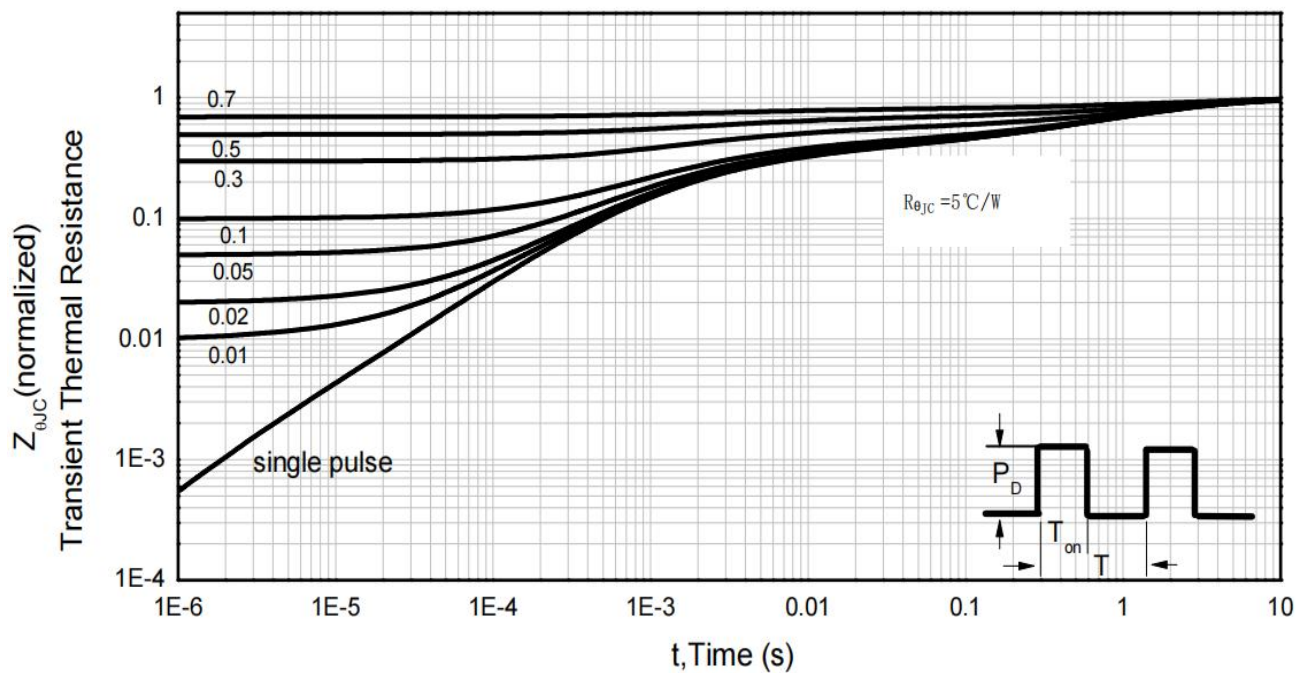
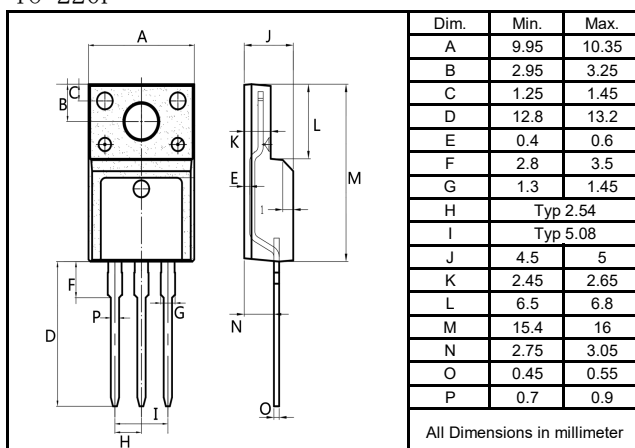


Figure 13: Normalized Maximum Transient Thermal Impedance (R_{thJC})

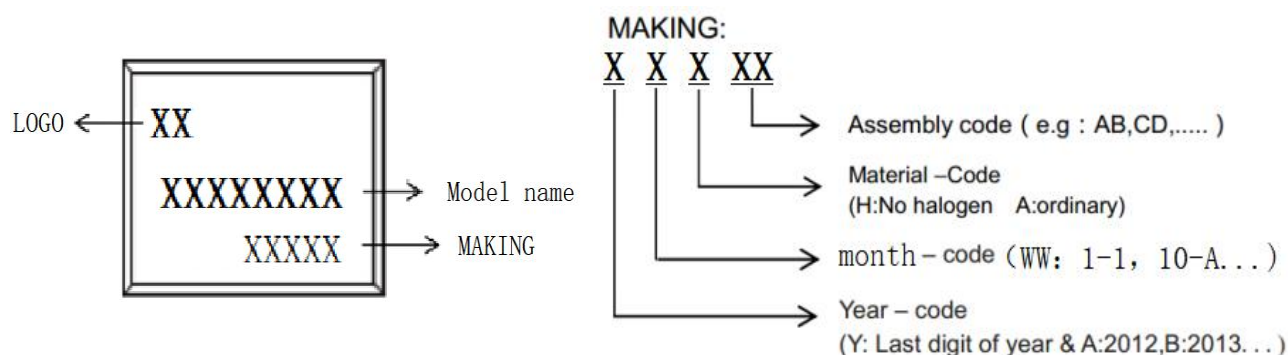


Package Outline Dimensions millimeters

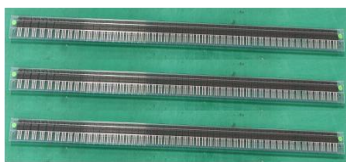
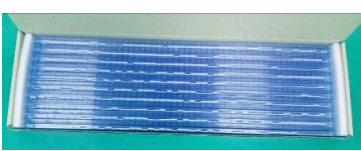
TO-220F



Marking on the body



packing instruction

PKG	Minimal Package	Mini Box	Box
TO-220F			
	50pcs/pdpe	1000pcs/box	5000pcs/box



LC65R950F

N-channel Super Junction MOSFET

Notice

All product, product specifications and data are subject to change without notice to improve. The right to explain is owned by LINGXUN electronics company.

Confirm that operation temperature is within the specified range described in the product specification. Avoid applying power exceeding normal rated

power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.

LINGXUN electronics shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

<http://www.lxmicro.com>

Revision History

Rev	Changes	Date
1.0	First version	2025-8-8